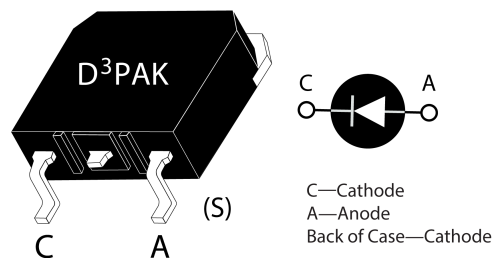


MSC030SDA170S Zero Recovery Silicon Carbide Schottky Diode

Product Overview

The silicon carbide (SiC) power Schottky barrier diode (SBD) product line from Microsemi increases the performance over silicon diode solutions while lowering the total cost of ownership for high-voltage applications. MSC030SDA170S is a 1700 V, 30 A SiC SBD in a TO-268 (D3PAK) package.



Features

The following are key features of the MSC030SDA170S device:

- No reverse recovery
- Low forward voltage
- Low leakage current
- Avalanche-energy rated
- RoHS compliant

Benefits

The following are benefits of the MSC030SDA170S device:

- High switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

Applications

The MSC030SDA170S device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
 - Switch-mode power supply
 - Inverters/converters
 - Motor controllers
- Freewheeling diode
 - Switch-mode power supply
 - Inverters/converters
- Snubber/clamp diode

Device Specifications

This section shows the specifications of the MSC030SDA170S device.

Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MSC030SDA170S device. $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Ratings	Unit
V_R	Maximum DC reverse voltage		1700	V
V_{RRM}	Maximum peak repetitive reverse voltage		1700	
V_{RWM}	Maximum working peak reverse voltage		1700	
I_F	Maximum DC forward current	$T_C = 25\text{ }^{\circ}\text{C}$	82	A
		$T_C = 135\text{ }^{\circ}\text{C}$	38	
		$T_C = 145\text{ }^{\circ}\text{C}$	31	
I_{FRM}	Repetitive peak forward surge current ($T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 8.3\text{ ms}$, half sine wave)		116	
I_{FSM}	Non-repetitive forward surge current ($T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 8.3\text{ ms}$, half sine wave)		353	
P_{TOT}	Total power dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	429	W
		$T_C = 110\text{ }^{\circ}\text{C}$	186	
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$, peak $I_L = 30\text{ A}$)		100	mJ

The following table shows the thermal and mechanical characteristics of the MSC030SDA170S device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		0.24	0.35	$^{\circ}\text{C}/\text{W}$
T_J, T_{STG}	Operating junction and storage temperature range	-55		175	$^{\circ}\text{C}$
T_L	Lead temperature for 10 seconds			300	$^{\circ}\text{C}$
Wt	Package weight		0.14		oz
			4.0		g

Electrical Performance

The following table shows the static characteristics of the MSC030SDA170S device. $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Forward voltage	$I_F = 30\text{ A}$, $T_J = 25\text{ }^{\circ}\text{C}$		1.5	1.8	V
		$I_F = 30\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$		2.25		
I_{RM}	Reverse leakage current	$V_R = 1700\text{ V}$, $T_J = 25\text{ }^{\circ}\text{C}$		4	200	μA
		$V_R = 1700\text{ V}$, $T_J = 175\text{ }^{\circ}\text{C}$		125		
Q_C	Total capacitive charge	$V_R = 900\text{ V}$		230		nC
C_J	Junction capacitance	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$		2070		pF
	Junction capacitance	$V_R = 600\text{ V}$, $f = 1\text{ MHz}$		167		
	Junction capacitance	$V_R = 900\text{ V}$, $f = 1\text{ MHz}$		138		

Typical Performance Curves

This section shows the typical performance curves of the MSC030SDA170S device.

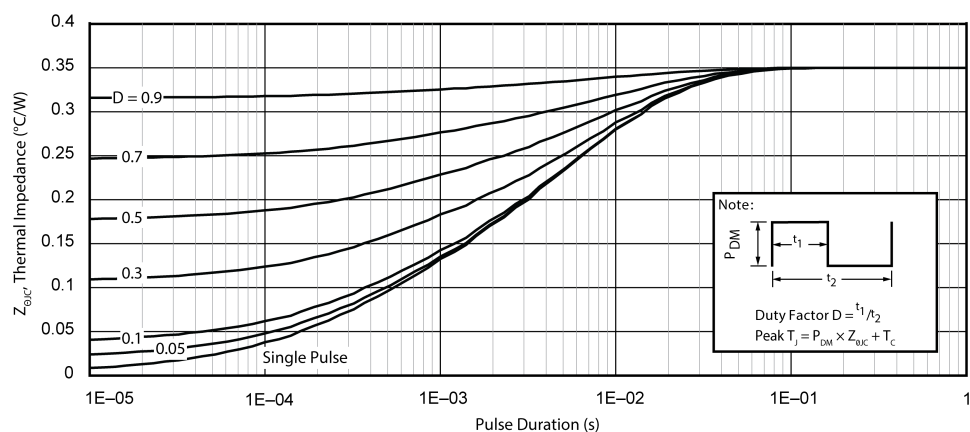


Figure 1 • Maximum Transient Thermal Impedance

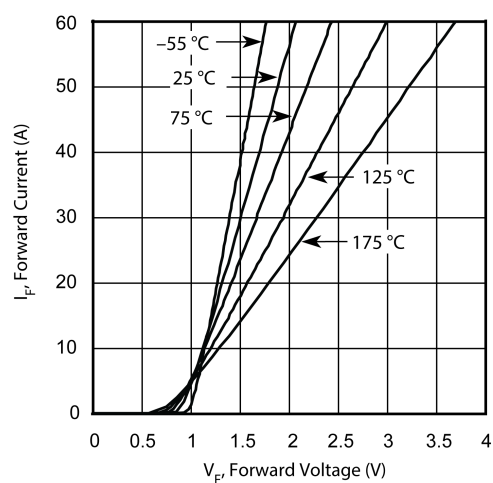


Figure 2 • Forward Current vs. Forward Voltage

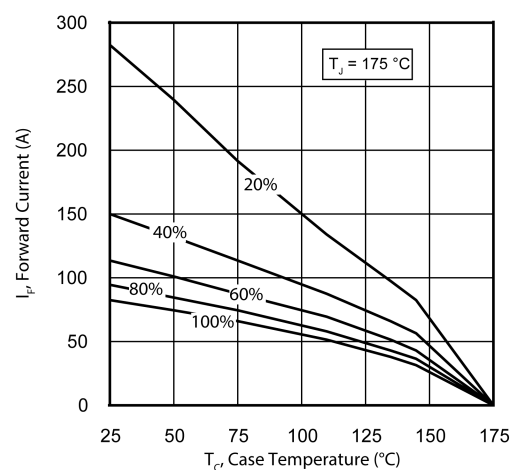


Figure 3 • Max. Forward Current vs. Case Temp.

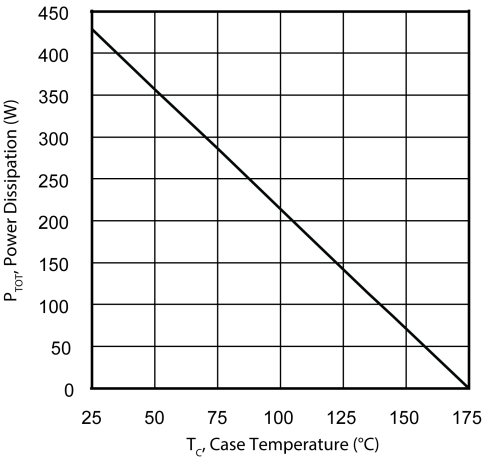


Figure 4 • Max. Power Dissipation vs. Case Temp.

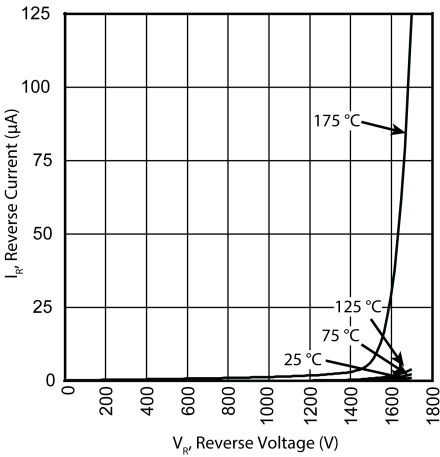


Figure 5 • Reverse Current vs. Reverse Voltage

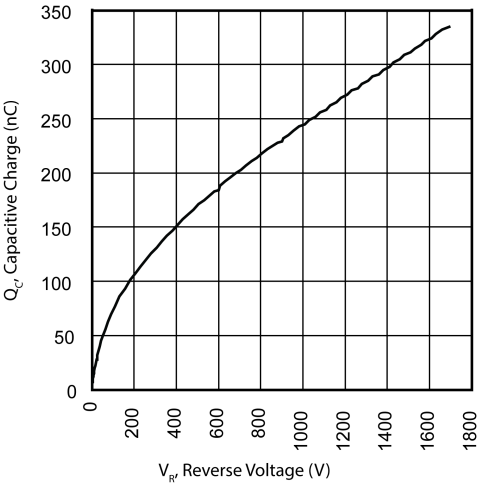


Figure 6 • Total Charge vs. Reverse Voltage

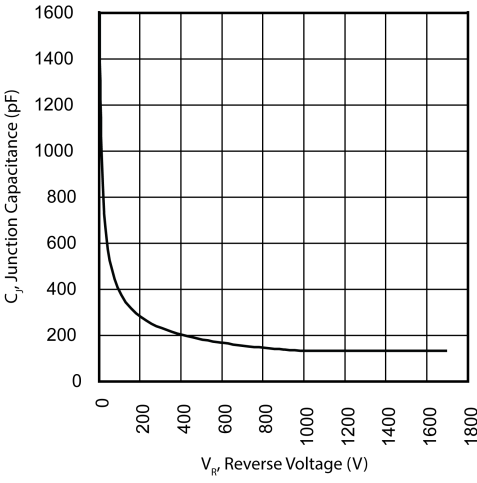


Figure 7 • Capacitance vs. Reverse Voltage

Package Specification

This section shows the package specification of the MSC030SDA170S device.

Package Outline Drawing

The following figure illustrates the TO-268 package outline of the MSC030SDA170S device.

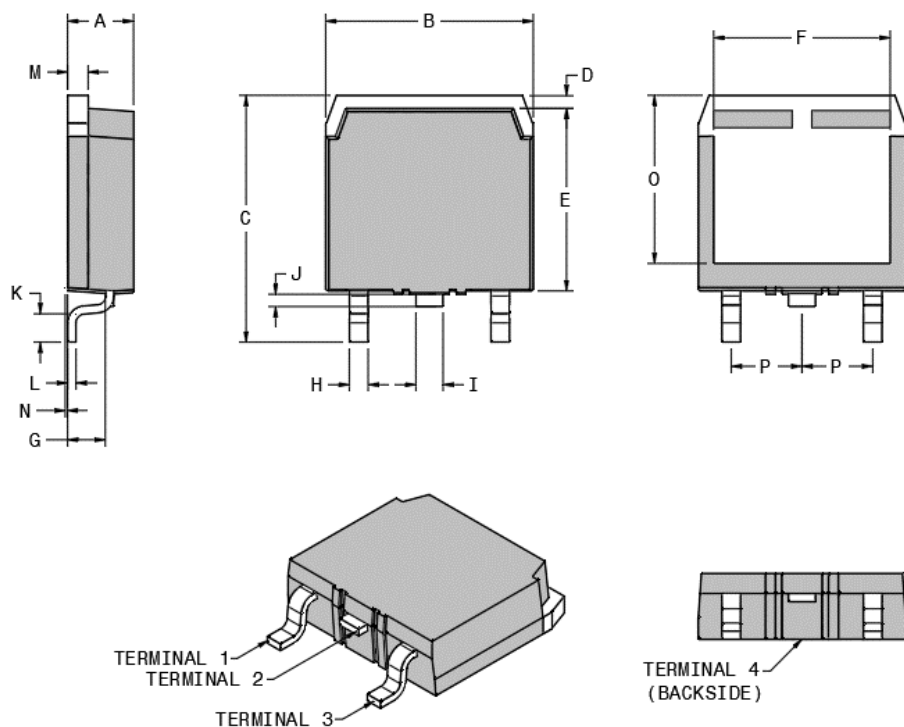


Figure 8 • Package Outline Drawing

The following table shows the TO-268 dimensions and should be used in conjunction with the package outline drawing.

Table 4 • TO-268 Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
A	4.90	5.10	0.193	0.201
B	15.85	16.20	0.624	0.638
C	18.70	19.10	0.736	0.752
D	1.00	1.25	0.039	0.049
E	13.80	14.00	0.543	0.551
F	13.30	13.60	0.524	0.535

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
G	2.70	2.90	0.106	0.114
H	1.15	1.45	0.045	0.057
I	1.95	2.21	0.077	0.087
J	0.94	1.40	0.037	0.055
K	2.40	2.70	0.094	0.106
L	0.40	0.60	0.016	0.024
M	1.45	1.60	0.057	0.063
N	0.00	0.18	0.000	0.007
O	12.40	12.70	0.488	0.500
P	5.45 BSC (nom.)		0.215 BSC (nom.)	
Terminal 1	Cathode			
Terminal 2	Cathode			
Terminal 3	Anode			
Terminal 4	Cathode			

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